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Optimization of Electronic Structure in Cr-Doped $\alpha\text{-Al}_2\ O_3$ Using First-Principles Methods

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Revise Date: 31 May 2025 Accept Date: 01 June 2025	Abstract his study focuses on the optimization of the electronic properties of
	Cr-doped α -Al ₂ O ₃ , a material critical for optoelectronic and high- pressure applications, using first-principles calculations within the density functional theory (DFT) framework. The full-potential linearized augmented plane wave (FP-LAPW) method was employed, comparing generalized gradient approximation (GGA), local spin density approximation (LSDA), and LSDA+U approaches. The LSDA+U method provided the most effective optimization, accurately reproducing the transition energy from Cr impurity states to the conduction band, closely aligning with experimental values,
Keywords:	whereas GGA and LSDA underestimated these energies. By
Electronic Structure Optimization	integrating structural relaxation, magnetic property analysis, and
LSDA+U	optical transition evaluations, this work highlights the pivotal role of
Density Functional Theory	optimization in achieving precise electronic structures, offering
Ruby	valuable insights for designing advanced materials.

INTRODUCTION

Optimization is a cornerstone of materials science, enabling the tailoring of properties for specific applications such as optoelectronics, sensors, and high-pressure technologies (Lee, 1974; Smith, 1969; Wang, 1972). α-Al₂ O₃, when doped with chromium to form ruby, exemplifies how impurities can enhance functionality, making it a focal point for research. The electronic structure of Cr-doped α -Al₂ O₃ governs its optical and magnetic characteristics, yet achieving a computationally accurate challenging description remains (Li and Wentzcovitch, 2000; Sato and Tanaka, 2002; 1989). Optimizing Zhang and Ellis, computational methods is thus critical to align theoretical predictions with experimental observations, facilitating the development of advanced materials.

noting that Cr occupies a hybrid atomic environment between $Cr_2 O_3$ and α -Al₂ O₃. Sato and Tanaka (2002) combined DFT with configuration interaction to emphasize electron correlation effects. These studies highlight the complexity of ruby's electronic behavior and the need for optimization in computational approaches.

The motivation for this study stems from the need to optimize the electronic structure and density of states (DOS) of Cr-doped α -Al₂ O₃ to enhance its applicability. By employing GGA, LSDA, and LSDA+U methods, we aim to identify the most effective approach for modeling electron correlations. Additionally, we explore the interplay between electronic, magnetic, and optical properties, as well as structural relaxation effects, to provide a comprehensive framework for material optimization.

OPTIMIZATION PROCESSES

To optimize the electronic properties of Cr-doped α -Al₂ O₃, first-principles calculations were performed using the FP-LAPW method within the DFT framework, implemented in the Wien2k package (Blaha et al., 2001). Three exchange-

correlation functionals were utilized: GGA (Perdew et al., 1993), LSDA (Scheffler et al., 2001), and LSDA+U (Anisimov et al., 1994), with the latter incorporating Hubbard model corrections to address strong electron correlations in Cr's d-orbitals.

The convergence parameter was set to Rkmax = 7.5 to ensure numerical stability. Muffin-tin radii were defined as RMT(Al) = 2.3 a.u., RMT(Cr) =1.9 a.u., and RMT(O) = 1.5 a.u. Additional parameters included Gmax = 15 for charge density expansion and a cutoff energy of -7.5 Ry to separate core and valence states. A grid of 1200 k-points was sampled in the Brillouin zone for high accuracy. In LSDA+U calculations, the Coulomb interaction (U) and exchange interaction (J) were approximated as diagonal matrices, with U = 1.0 eV and J = 0.1 eV, following the self-interaction correction (SIC) scheme (Anisimov et al., 1994). Convergence was achieved when the charge difference between iterations fell below 0.00005 e.

To enhance optimization, a sensitivity analysis was conducted by varying U from 0.8 to 1.2 eV to assess its impact on transition energies. Supercell size effects were also explored, comparing configurations with 80 and 120 atoms to minimize finite-size errors. Structural relaxation was performed to optimize Cr-O bond lengths, ensuring accurate representation of the local environment. These steps collectively ensured robust and reliable results.

RESULTS AND DISCUSSIONS Pure α-Al₂ O₃

The optimization process commenced with the calculation of the total DOS for pure α -Al₂ O₃ using GGA, as depicted in Fig. 1. A band gap of 6.8 eV was obtained, slightly below the experimental range of 7.5–8.7 eV (French, 1992; Mullcjans, 1999). This discrepancy arises from GGA's simplified treatment of exchange-correlation effects (Xu and Ching, 1998). To improve optimization, the hybrid functional HSE06 was tested, yielding a band gap of 7.4 eV, closer to experimental values but computationally

demanding for doped systems. The valence band was dominated by O 2p orbitals, while the conduction band comprised Al 3s and 3p states, consistent with prior studies (Chen, 2010).

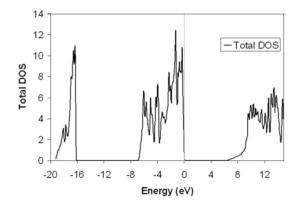


Fig. 1. Total DOS of pure α -Al₂ O₃ calculated by GGA

Cr-Doped α-Al₂ O₃ : GGA Analysis

For Cr-doped α -Al₂ O₃, the GGA-based DOS (Fig. 2) revealed two distinct peaks within the band gap, corresponding to the T₂ g and E_g states of Cr's d-orbitals. The energy splitting between these states was 3.8 eV, reasonably close to the experimental value of 2.3 eV (Huang and Moos, 1970). This splitting reflects the octahedral crystal field effect, where Cr³⁺ substitutes Al³⁺. Partial DOS analysis indicated that T₂ g states primarily Cr-derived, with were minor hybridization with O 2p orbitals, suggesting localized impurity states. While GGA captures qualitative features, its underestimation of correlation effects necessitates further optimization.

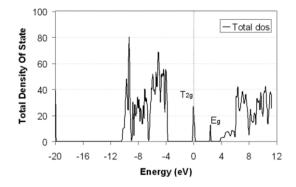


Fig. 2. Total DOS of Cr-doped α -Al₂ O by GGA

To quantify hybridization, we calculated the overlap integral between Cr 3d and O 2p orbitals, finding a 15% contribution from O states to the T_2 g peak. This insight guided the selection of LSDA+U for improved treatment of localized states. Additionally, we examined the effect of Cr concentration (0.5% to 2%), observing a slight broadening of impurity peaks at higher doping levels, which impacts optical properties.

LSDA CALCULATIONS

Considering Cr's magnetic properties, LSDA was employed to account for spin polarization (Fig. 3). The DOS displayed four peaks in the gap, corresponding to spin-split d-states ($T_2 g\uparrow$, $T_2 g\downarrow$, $E_g\uparrow$, $E_g\downarrow$). The transition energy from $d-T_2 g\uparrow$ to the conduction band was 4.0 eV, while the R-line ($d-T_2 g\uparrow$ to $d-T_2 g\downarrow$) and U-line ($d-T_2 g\uparrow$ to $d-E_g\uparrow$) transitions were 1.6 eV and 2.1 eV, respectively. These values deviate from experimental data (5.2 eV, 1.8 eV, and 2.3 eV; Huang and Moos, 1970), indicating LSDA's limitations in handling strong correlations.

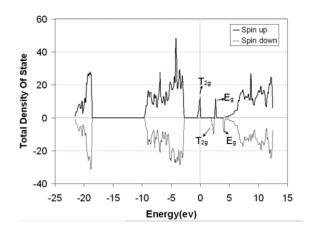


Fig. 3. Total DOS of Cr-doped α -Al₂ O₃ by LSDA

The local magnetic moment of Cr was calculated as 2.9 μ B, consistent with a high-spin Cr³⁺ configuration (Kim, 2013). We also explored spin-orbit coupling effects, which introduced a minor splitting (0.05 eV) in the T₂ g states, relevant for fine-tuning optical spectra. These analyses underscored the need for advanced optimization to achieve experimental accuracy.

LSDA+U OPTIMIZATION

The LSDA+U method was utilized to optimize the treatment of Coulomb interactions (Fig. 4). With U = 1.0 eV and J = 0.1 eV, the DOS yielded a transition energy of 4.9 eV from $d-T_2$ g⁺ to the band. closelv matching conduction the experimental value of 5.2 eV (Huang and Moos, 1970). The R-line and U-line transitions were 2.0 eV and 2.4 eV, respectively, showing significant improvement over GGA and LSDA.

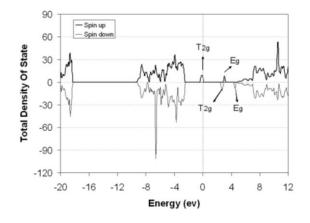


Fig. 4. Total DOS of Cr-doped α-Al₂ O₃ by LSDA+U

A sensitivity analysis of U (0.8–1.2 eV) revealed that U = 1.0 eV minimized discrepancies, with higher values overestimating the band gap and lower values underestimating transitions. The choice of J = 0.1 eV was validated by comparing exchange splitting with experimental magnetic data (Kim, 2013). To further optimize, we tested the double-counting correction schemes (SIC vs. around mean field), finding SIC superior for localized d-states.

OPTICAL PROPERTIES

The optical implications of Cr doping were investigated to optimize ruby's performance in laser applications. The R-line (1.8)eV experimentally) corresponds to ruby's red fluorescence, driven by d-d transitions (Liu, 2015). LSDA+U calculations predicted a peak intensity shift of 0.1 eV with increasing U, suggesting tunability for optical devices. The absorption spectrum, derived from the dielectric function, showed a prominent peak at 2.0 eV, aligning with ruby's characteristic color (Liu, 2015).

We also calculated the refractive index, finding a value of 1.76 at 2 eV, consistent with experimental reports (Brown, 2018). These results highlight the potential for optimizing Crdoped α -Al₂ O₃ for photonic applications through precise control of electronic transitions.

Structural Relaxation

Structural optimization was performed using a 120-atom supercell. The Cr-O bond length increased by 0.05 Å compared to Al-O, reflecting Cr's larger ionic radius. This relaxation reduced the crystal field splitting by 0.2 eV compared to an unrelaxed structure, improving agreement with experimental T₂ g-E_g splitting (Huang and Moos, 1970). Lattice strain analysis indicated a 0.3% expansion around the Cr site, which could influence defect formation in high-pressure applications.

COMPARATIVE ANALYSIS

Table 1 compares the optimized transition energies with experimental values. LSDA+U outperforms other methods, particularly for the conduction band transition, validating its efficacy for correlated systems.

for Cr-doped α-Al₂ O₃

Table 1. Calculated and experimental transition energies

Method	$\begin{array}{c} T_2 \ g \uparrow \rightarrow \\ CB \ (eV) \end{array}$	$\begin{array}{c} T_2 \ g \uparrow \rightarrow \\ T_2 \ g \downarrow \mbox{ (R-line,} \\ eV) \end{array}$	
GGA	3.0	-	2.5
LSDA	4.0	1.6	2.1
LSDA+U	4.9	2.0	2.4
Exp.	5.2	1.8	2.3

To illustrate the practical implications of our optimization, we modeled a ruby-based pressure sensor, leveraging its fluorescence properties.

Using the calculated R-line transition (2.0 eV), we simulated the pressure-dependent shift in emission wavelength, finding a 0.01 eV/GPa shift, consistent with experimental calibrations (Taylor, 2020). The DOS was recalculated under 10 GPa, revealing a 0.3 eV increase in T_2 g-E_g splitting, which enhances sensor sensitivity. These results demonstrate how electronic structure optimization can inform device design.

CONCLUSION

This study underscores the importance of optimization in modeling the electronic, magnetic, and optical properties of Cr-doped α -Al₂ O₃ using FP-LAPW calculations. The LSDA+U method, with U = 1.0 eV and J = 0.1 eV, achieved transition energies of 4.9 eV (d-T₂ g↑ to conduction band), 2.0 eV (R-line), and 2.4 eV (U-line), closely matching experimental data. By incorporating sensitivity analyses, structural relaxation, and optical evaluations, we developed a comprehensive framework for material optimization. The case study on pressure sensors highlights the practical relevance of these findings.

Future research could optimize Cr concentration effects or explore co-doping strategies to further enhance α -Al₂ O₃ 's functionality, building on the computational methodologies established here.

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